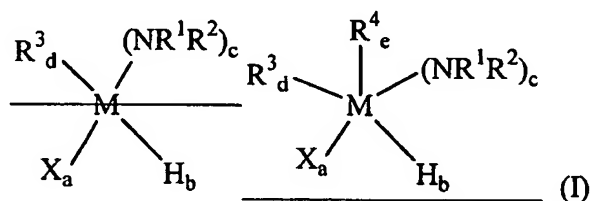


hydride elimination. Thus, preferred bulky groups contain a hydrogen bonded to the carbon in the beta position to the germanium. --

Please delete the paragraph beginning with "Accordingly, the present . . ." at page 14, line 9, and replace it with the following new paragraph:

SB 4-30-08

-- Accordingly, the present invention provides a device for feeding a fluid stream saturated with an organometallic compound suitable for depositing a metal film containing silicon, germanium, and combinations thereof to a chemical vapor deposition system including a vessel having an elongated cylindrical shaped portion having an inner surface having a cross-section, a top closure portion and a bottom closure portion, the top closure portion having an inlet opening for the introduction of a carrier gas and an outlet opening, the elongated cylindrical shaped portion having a chamber containing one or more organometallic compounds of formula I



wherein M is Si or Ge; R^1 and R^2 are independently chosen from H, alkyl, alkenyl, alkynyl and aryl; each R^3 is independently chosen from $(\text{C}_1\text{-C}_{12})$ alkyl, alkenyl, alkynyl and aryl, provided that R^3 is not cyclopentadienyl; each R^4 is independently chosen from $(\text{C}_3\text{-C}_{12})$ alkyl; X is halogen; $a = 0\text{-}3$; $b = 0\text{-}3$; $c = 0\text{-}3$; $d = 0\text{-}2$; $e = 0\text{-}4$; and $a + b + c + d + e = 4$; wherein $\text{R}^3 \neq \text{R}^4$; wherein the sums of $a + b$ and $a + d$ are each ≤ 3 ; provided that when $\text{M} = \text{Si}$ the sum of $b + c$ is ≤ 3 ; the inlet opening being in fluid communication with the chamber and the chamber being in fluid communication with the outlet opening. --